6. (Amended) The method of fabricating a nitride semiconductor device of claim 5, wherein said second nitride semiconductor layer is an active layer.

7. (Amended) The method of fabricating a nitride semiconductor device of claim 13, wherein the step of growing said first nitride semiconductor layer and the step of growing said second nitride semiconductor layer are conducted at different growth temperatures.

8. (Twice amended) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising the steps of:

forming plural seed crystals on a substrate;

selectively growing, on said substrate, a first nitride semiconductor layer including aluminum from said plural seed crystals under a first growth ambient pressure; and

growing, on said first nitride semiconductor layer, a second nitride semiconductor layer under a second growth ambient pressure different from said first growth ambient pressure,

wherein said first growth ambient pressure is lower than said second growth ambient pressure, and is lower than the atmospheric pressure.

Please add new claim 13.

--13. (New) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

a step of growing, on a substrate, a first nitride semiconductor layer including aluminum and/or magnesium under a first growth ambient pressure; and

a step of growing a second nitride semiconductor layer, which is adjacent to said first nitride semiconductor layer and does not include aluminum and magnesium, under a second growth ambient pressure,

wherein said first growth ambient pressure is lower than said second growth ambient pressure, and is lower than the atmospheric pressure.